

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

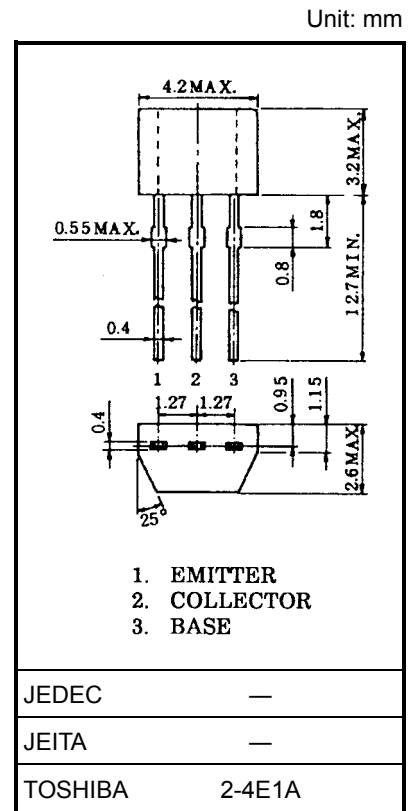
2SC2459

Audio Amplifier Applications

- High breakdown voltage: $V_{CEO} = 120\text{ V (max)}$
- High DC current gain: $h_{FE} = 200\sim700$
- Excellent h_{FE} linearity: $h_{FE}(I_C = 0.1\text{ mA})/h_{FE}(I_C = 2\text{ mA}) = 0.95$ (typ.)
- Low noise: $NF = 1\text{ dB (typ.)}$, 10 dB (max)
- Complementary to 2SA1049.
- Small package.

Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	120	V
Collector-emitter voltage	V_{CEO}	120	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Base current	I_B	20	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$

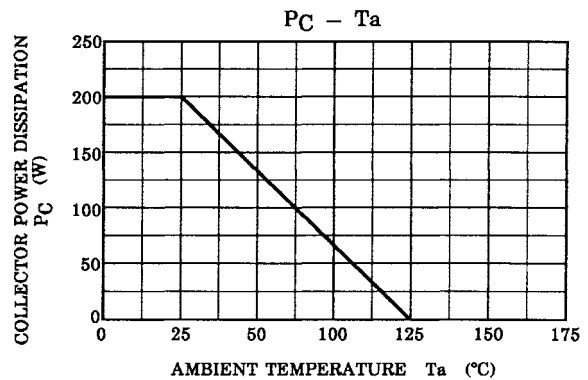
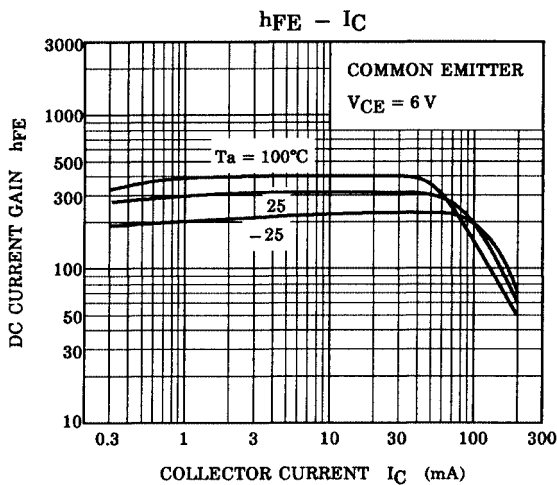
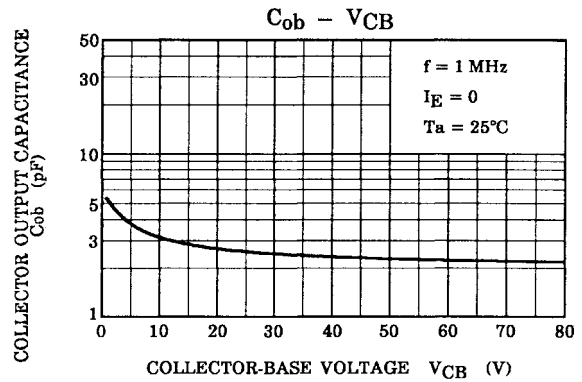
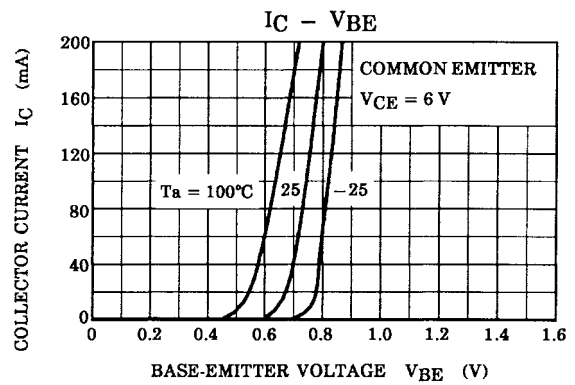
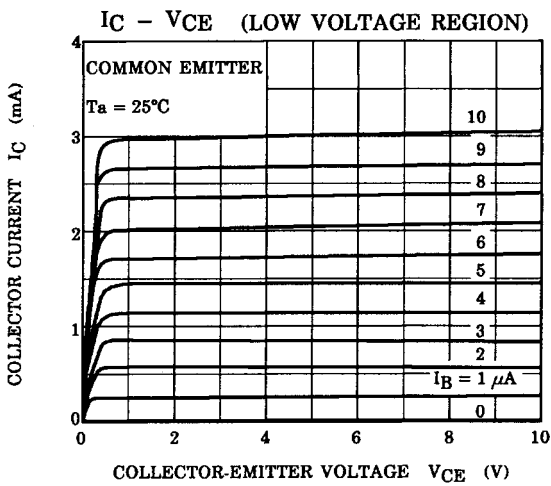
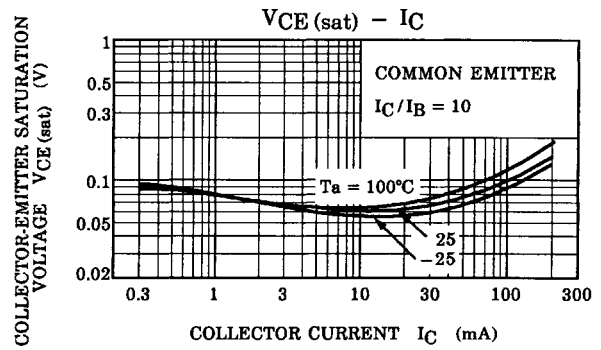
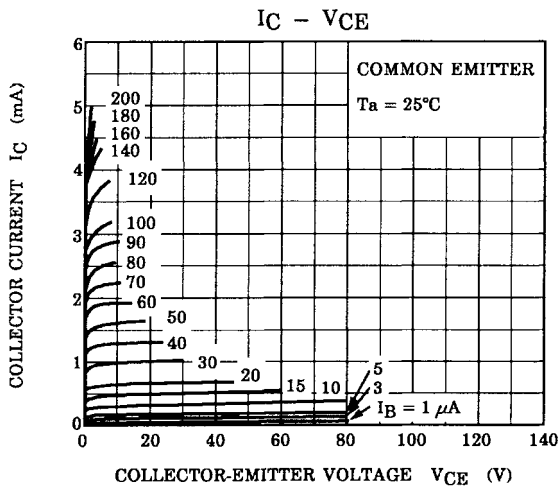


Weight: 0.13 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 120\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	0.1	μA
DC current gain	h_{FE} (Note)	$V_{CE} = 6\text{ V}, I_C = 2\text{ mA}$	200	—	700	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	—	—	0.3	V
Transition frequency	f_T	$V_{CE} = 6\text{ V}, I_C = 1\text{ mA}$	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	3.0	—	pF
Noise figure	NF	$V_{CE} = 6\text{ V}, I_C = 0.1\text{ mA},$ $f = 1\text{ kHz}, R_G = 10\text{ k}\Omega$	—	1.0	10	dB

Note: h_{FE} classification GR: 200~400, BL: 350~700



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